

P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μPA1818 is a switching device which can be driven directly by a 2.5 V power source.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power management of notebook computers and so on.

FEATURES

- 2.5 V drive available
- Low on-state resistance
 $R_{DS(on)1} = 15.2 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.5 \text{ V, } I_D = -5.0 \text{ A)}$
 $R_{DS(on)2} = 16 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -5.0 \text{ A)}$
 $R_{DS(on)3} = 25 \text{ m}\Omega \text{ MAX. (} V_{GS} = -2.5 \text{ V, } I_D = -5.0 \text{ A)}$
- Built-in G-S protection diode against ESD

ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA1818GR-9JG	Power TSSOP8

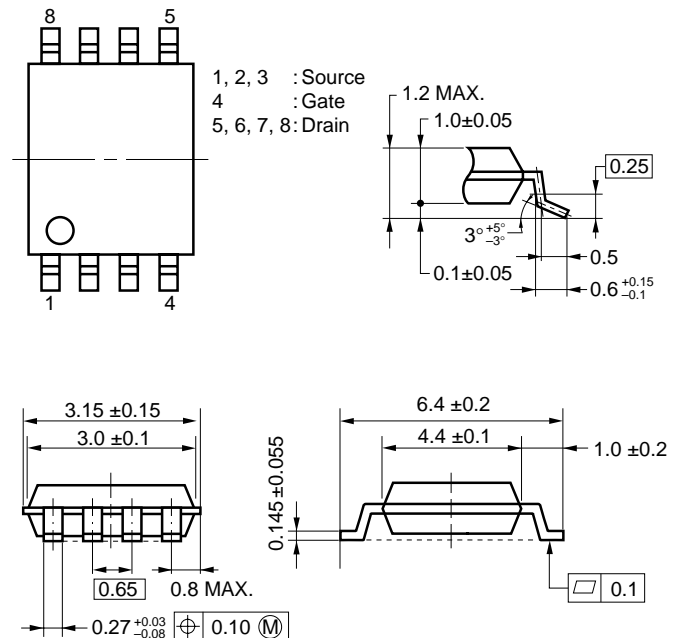
ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	-20	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±12	V
Drain Current (DC) (T _A = 25°C)	I _{D(DC)}	±10	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	±40	A
Total Power Dissipation ^{Note2}	P _T	2.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

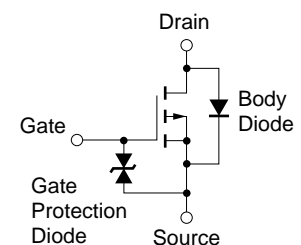
- Notes 1.** PW ≤ 10 μs, Duty Cycle ≤ 1%
2. Mounted on ceramic substrate of 5000 mm² x 1.1 mm

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT

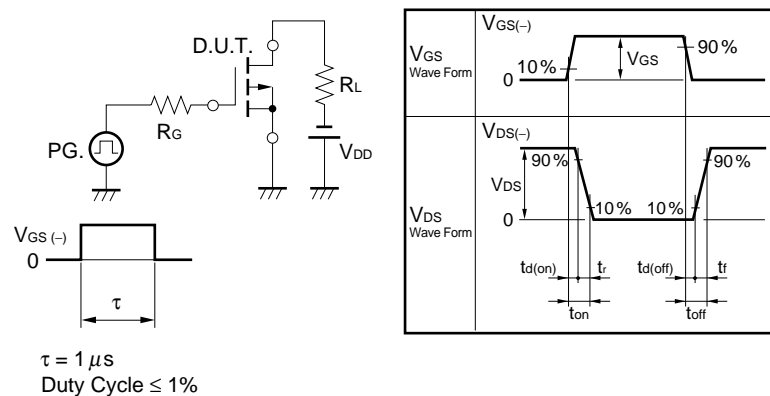


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 Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

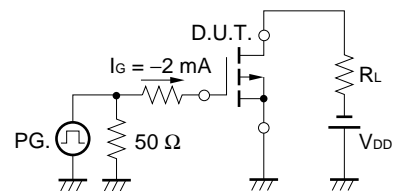
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V			-1.0	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±12 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1.0 mA	-0.5	-1.1	-1.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10 V, I _D = -5.0 A	12	24		S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = -4.5 V, I _D = -5.0 A		12.1	15.2	mΩ
	R _{DS(on)2}	V _{GS} = -4.0 V, I _D = -5.0 A		12.7	16	mΩ
	R _{DS(on)3}	V _{GS} = -2.5 V, I _D = -5.0 A		18.8	25	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V		2200		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		510		pF
Reverse Transfer Capacitance	C _{rss}	f = 1.0 MHz		310		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -10 V, I _D = -5.0 A		23		ns
Rise Time	t _r	V _{GS} = -4.0 V		207		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		139		ns
Fall Time	t _f			193		ns
Total Gate Charge	Q _G	V _{DD} = -16 V		20		nC
Gate to Source Charge	Q _{GS}	V _{GS} = -4.0 V		5.0		nC
Gate to Drain Charge	Q _{GD}	I _D = -10 A		6.0		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 10 A, V _{GS} = 0 V		0.82		V
Reverse Recovery Time	t _{rr}	I _F = 10 A, V _{GS} = 0 V		44		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		28		nC

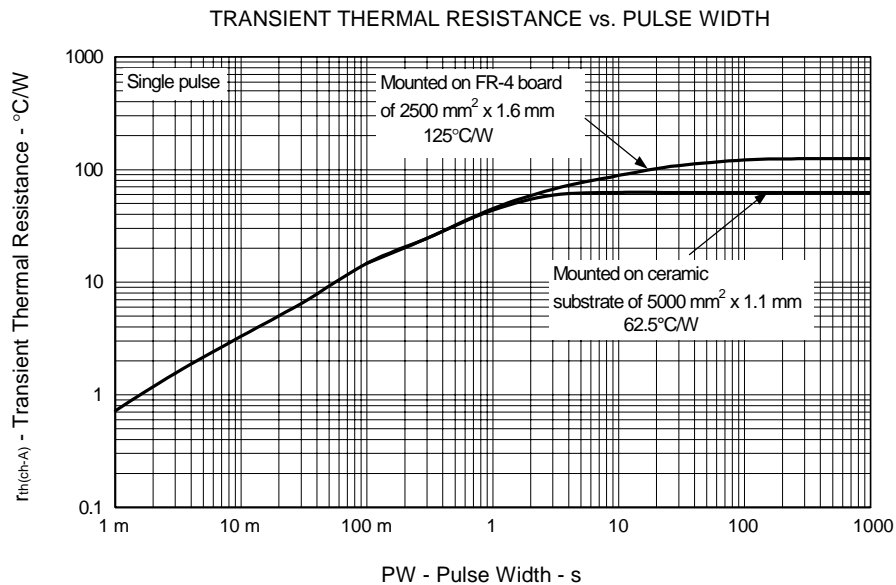
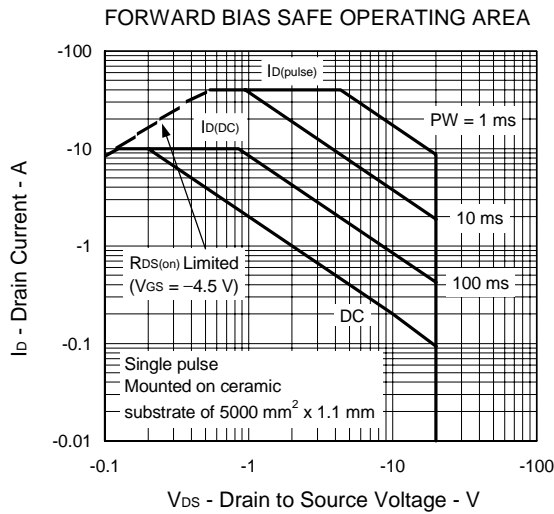
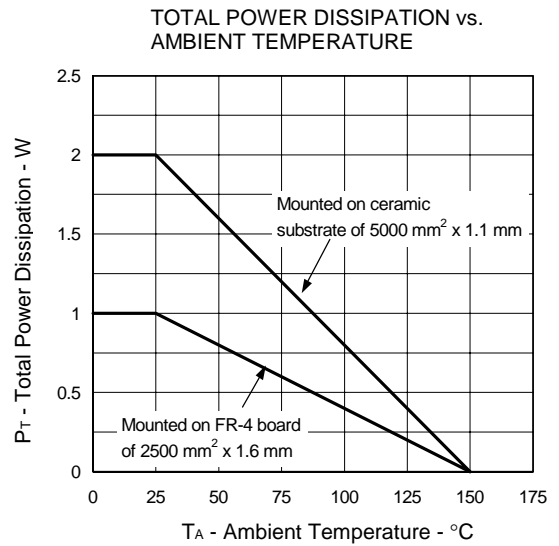
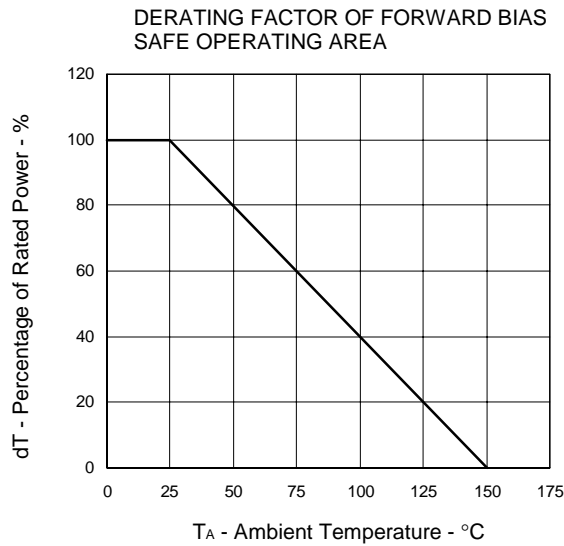
TEST CIRCUIT 1 SWITCHING TIME



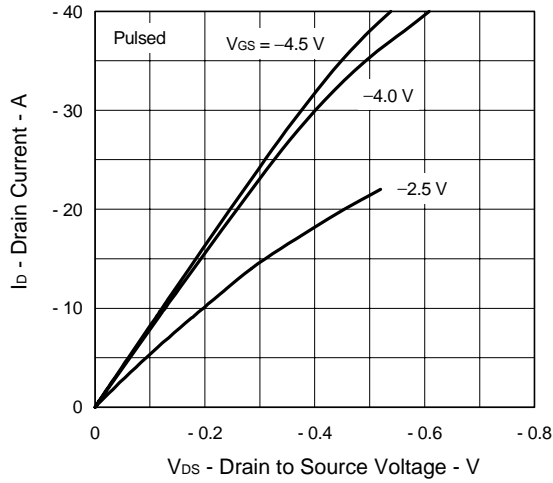
TEST CIRCUIT 2 GATE CHARGE



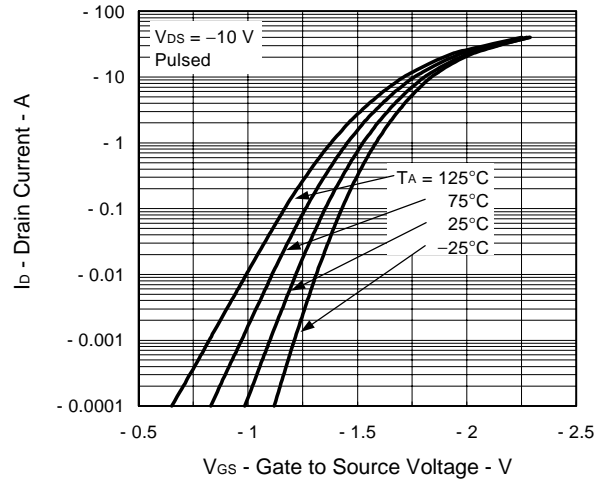
TYPICAL CHARACTERISTICS (T_A = 25°C)



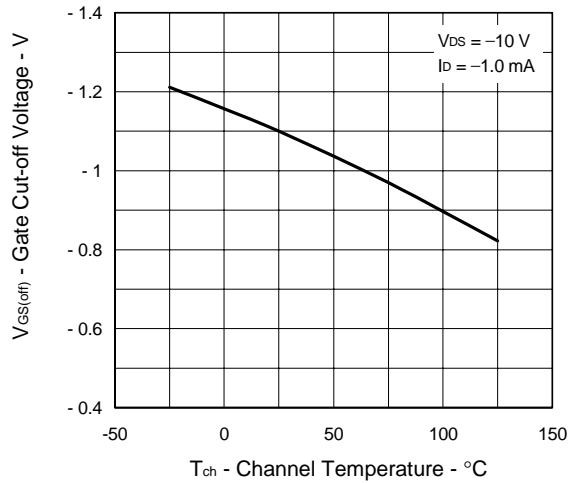
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



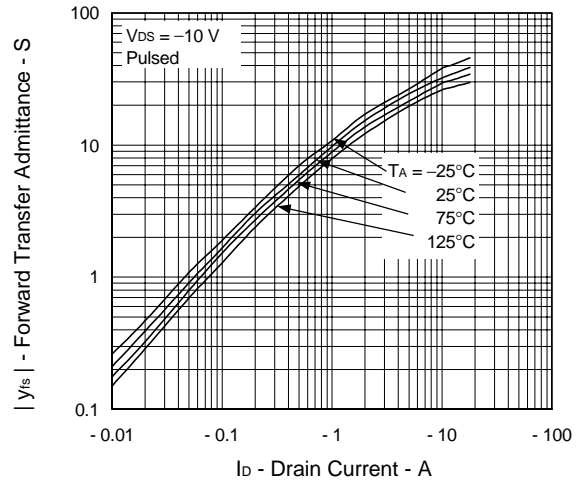
FORWARD TRANSFER CHARACTERISTICS



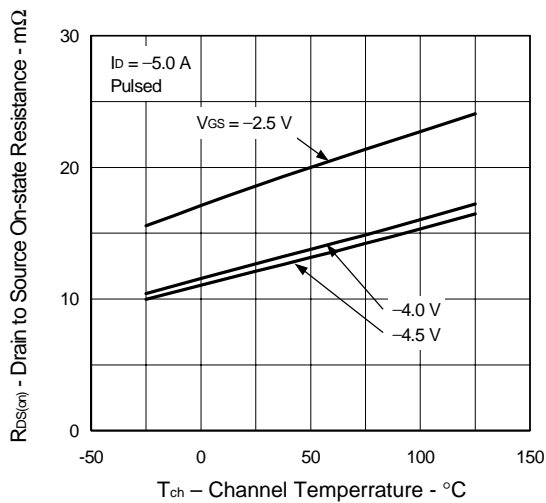
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



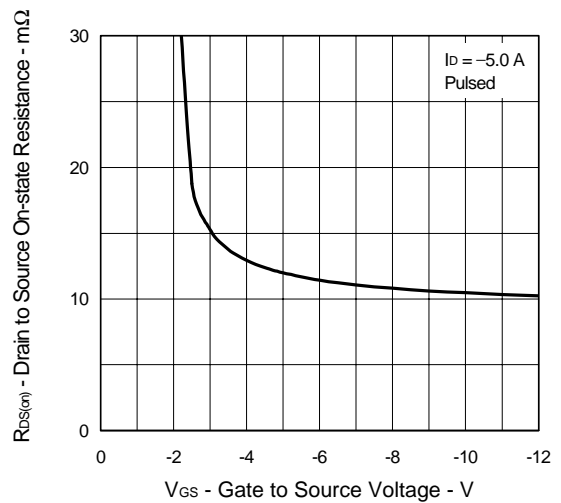
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

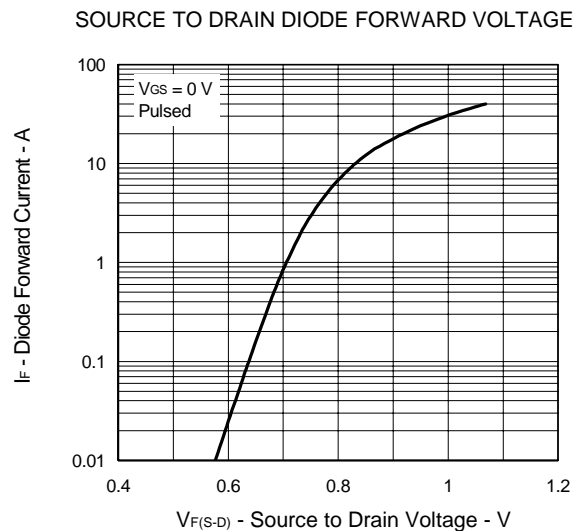
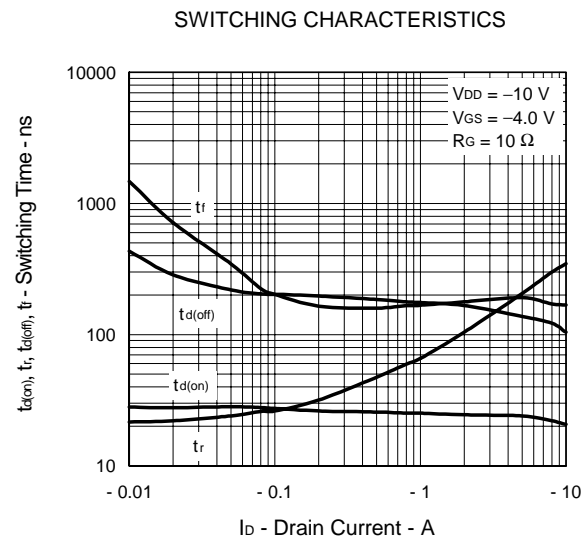
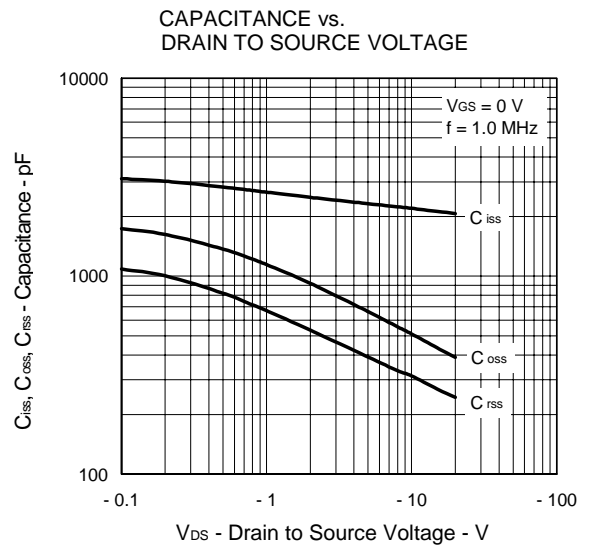
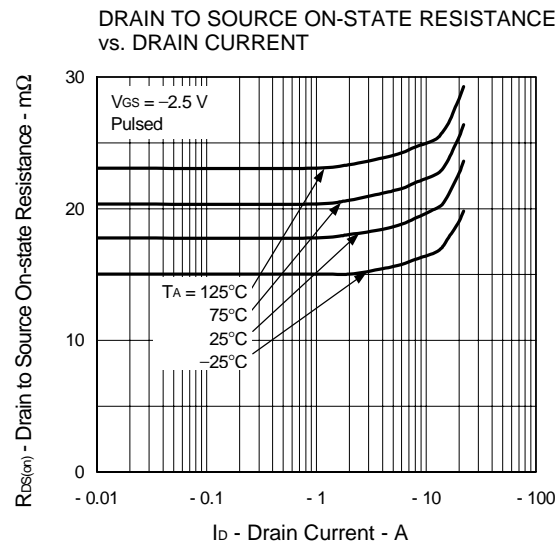
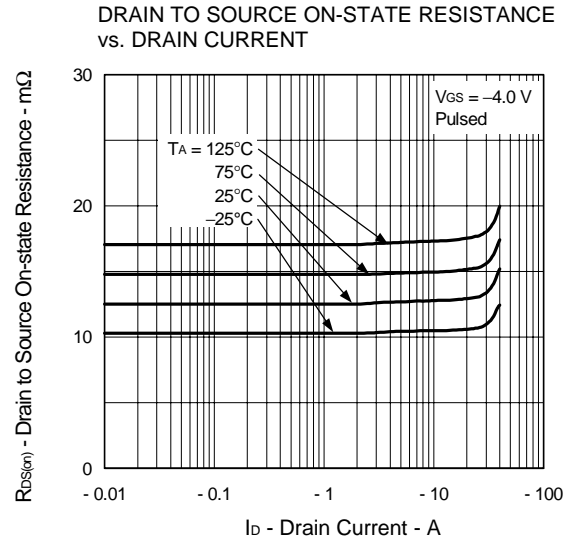
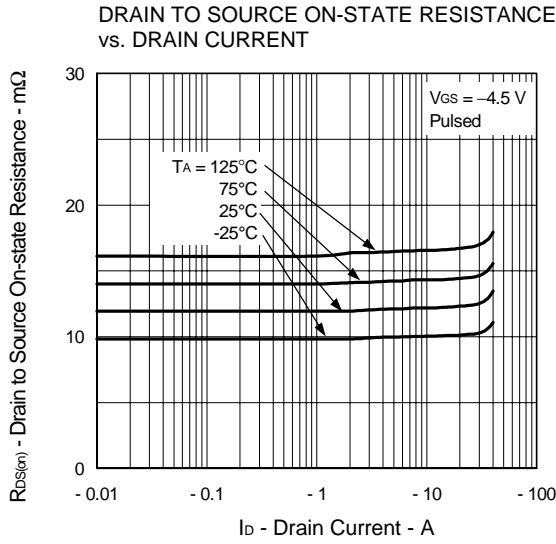


DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

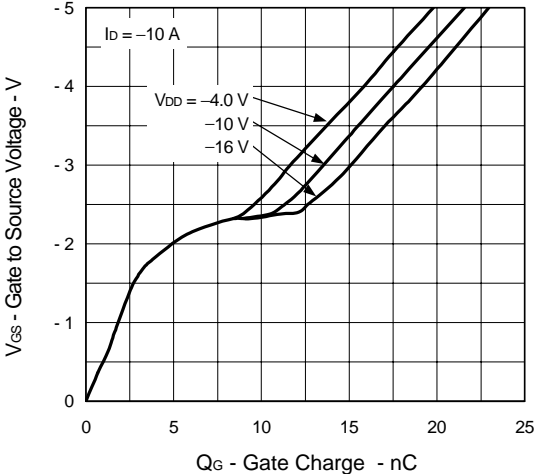


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE





DYNAMIC INPUT/OUTPUT CHARACTERISTICS



[MEMO]

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